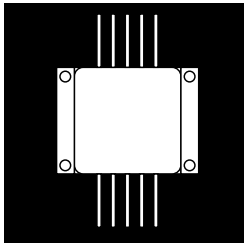


INSULATED GATE BIPOLAR TRANSISTOR (IGBT) IN A HERMETIC PACKAGE



1000 Volt, 75 Amp, N-Channel IGBT
In A Hermetic Metal Package

FEATURES

- Isolated IGBTs In A Hermetic Package
- High Input Impedance
- Low On-Voltage
- High Current Capability
- High Switching Speed
- Low Tail Current
- Available With Free Wheeling Diodes
- Available Screened To MIL-S-19500, TX, TXV and S Levels

DESCRIPTION

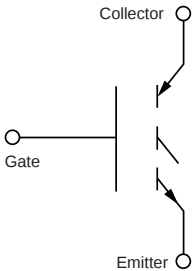
This IGBT power transistor features the high switching speeds of a power MOSFET and the low on-resistance of a bipolar transistor. It is ideally suited for high power switching applications such as frequency converters for 3Ø motors, UPS and high power SMPS.

MAXIMUM RATINGS @ 25 C Unless Specified Otherwise

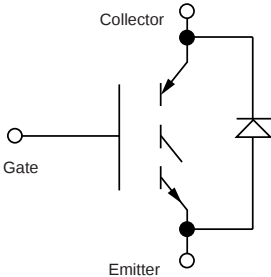
PART NUMBER	I _C (Cont.) @ 90°C, A	V _{(BR)CES} V	V _{CE(sat)} (Typ.) V	T _f (Typ.) ns	q _{JC} °C/W	P _D W	T _J °C
OM6535SF	75	1000	4.0	400	.40	315	150
OM6536SF	75	1000	4.0	400	.40	315	150

3.1

SCHEMATICS

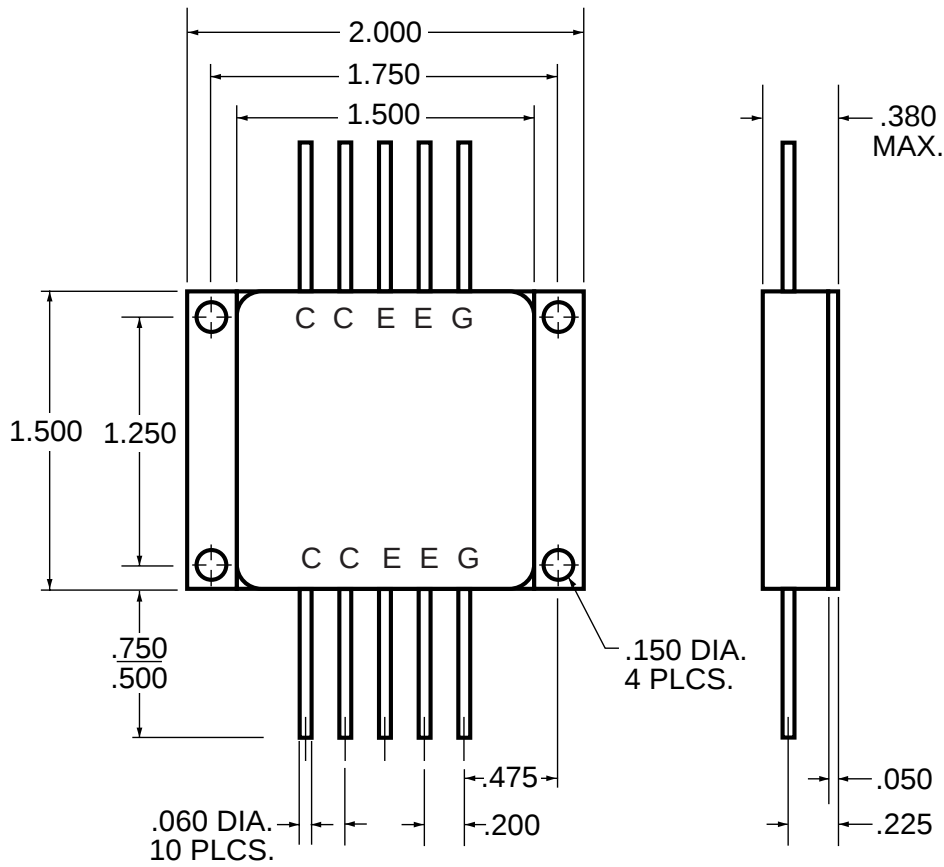


OM6535SF



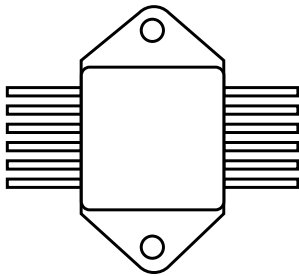
OM6536SF
(with Diode)

MECHANICAL OUTLINE

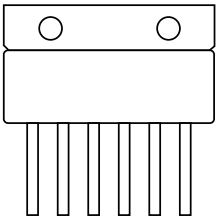


3.1

PACKAGE OPTIONS



MOD PAK



6 PIN SIP

Note: IGBTs are also available in Z-tab, dual and quad pak styles.
Please call the factory for more information.